General Description

The SN4435A is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the synchronous buck converter applications .

The SN4435A meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

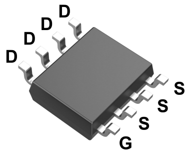
Product Summery

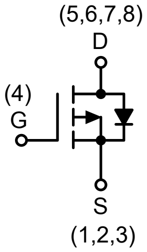
BV_{DSS}	R_{DSON}	I_D
-30V	20mΩ	-8A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOP-8L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-8	A
I_D@T_C=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-6.5	A
I_{DM}	Pulsed Drain Current[2]	-32	A
EAS	Single Pulse Avalanche Energy[3]	64	mJ
I_{AS}	Avalanche Current	-16	A
P_D@T_A=25℃	Total Power Dissipation[4]	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	90	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	50	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.022	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-8.2A	---	20	23	mΩ
		V_{GS}=-4.5V , I_D=-4A	---	25	33	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.5	-2.0	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-6A	---	11	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-8.2A	---	21	---	nC
Q_{gs}	Gate-Source Charge		---	2.6	---	
Q_{gd}	Gate-Drain Charge		---	6.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=6Ω, I_D=-6A ,R_L=15Ω,	---	8	---	ns
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	16	---	
T_f	Fall Time		---	32	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	1000	---	pF
C_{oss}	Output Capacitance		---	210	---	
C_{rss}	Reverse Transfer Capacitance		---	150	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=-25V , L=0.5mH , I_{AS}=-16A	49	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	-2.0	A
I_{SM}	Pulsed Source Current[2,6]		---	---	-32	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-8A , dI/dt=100A/μs , T_J=25℃	---	16.3	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.9	---	nC

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.5mH,I_{AS}=-16A

4.The power dissipation is limited by 150℃ junction temperature

5.The Min. value is 100% EAS tested guarantee.

6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

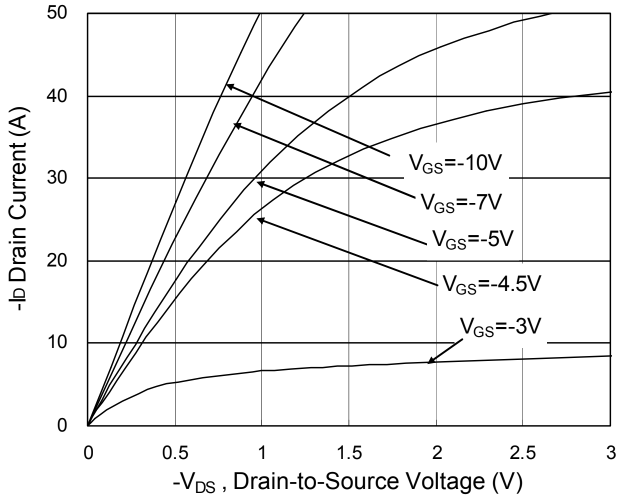


Fig.1 Typical Output Characteristics

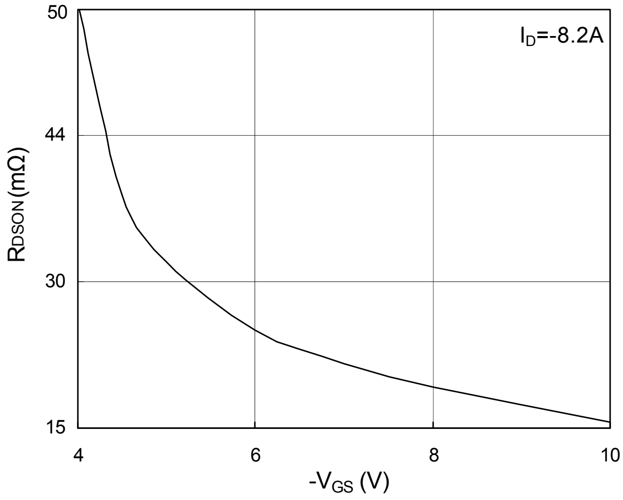


Fig.2 On-Resistance v.s Gate-Source

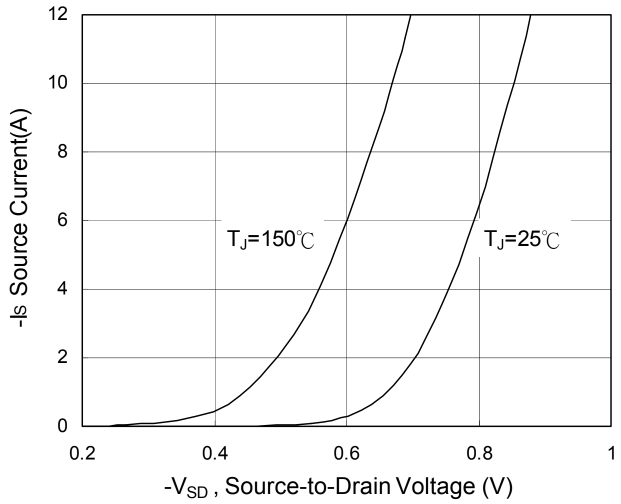


Fig.3 Forward Characteristics of Reverse

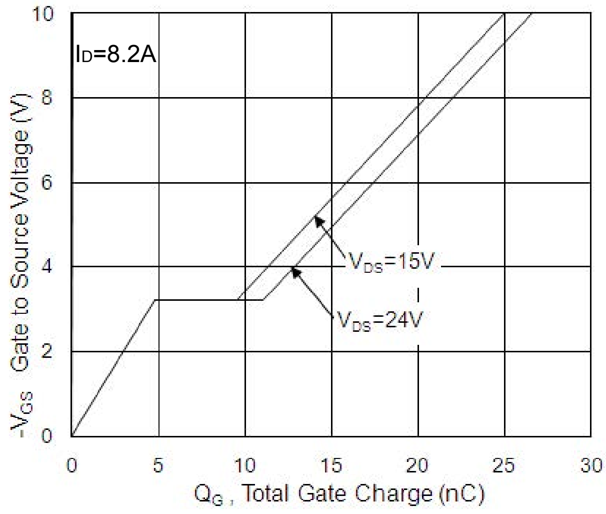


Fig.4 Gate-Charge Characteristics

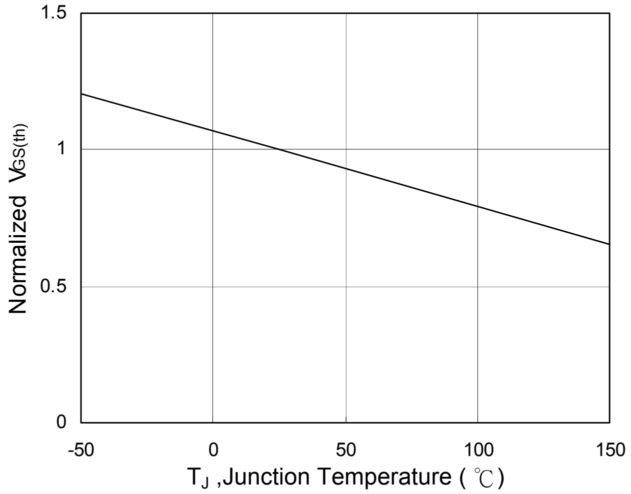


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

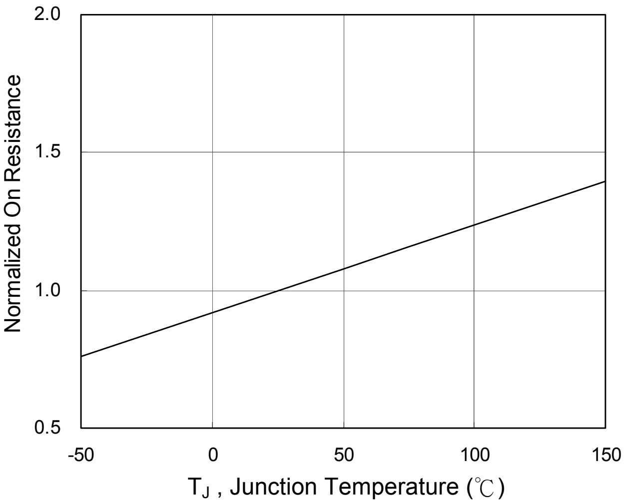


Fig.6 Normalized R_{DSON} vs. T_J

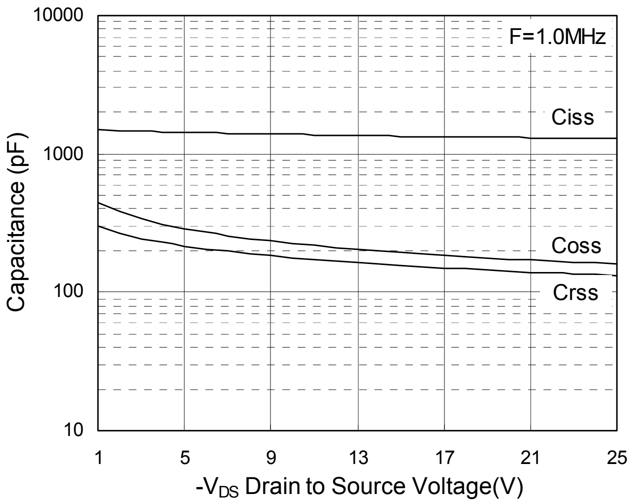


Fig.7 Capacitance

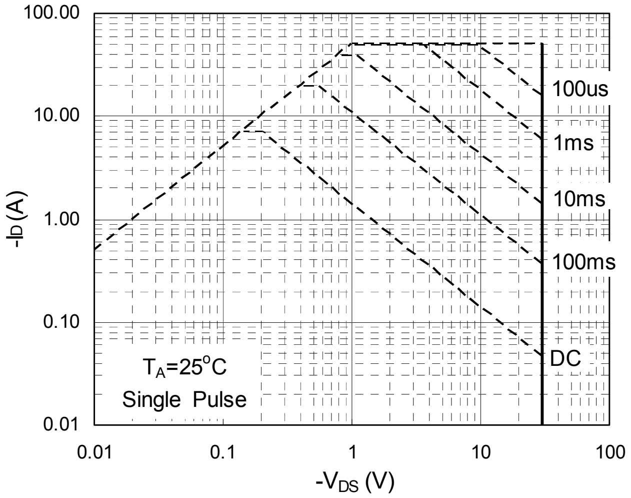


Fig.8 Safe Operating Area

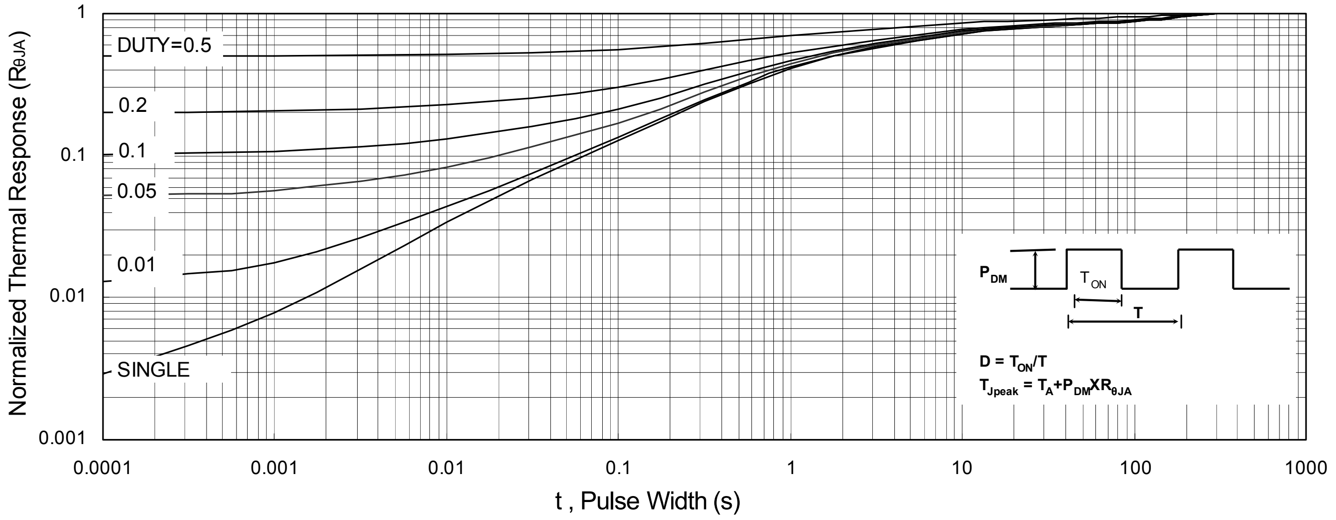
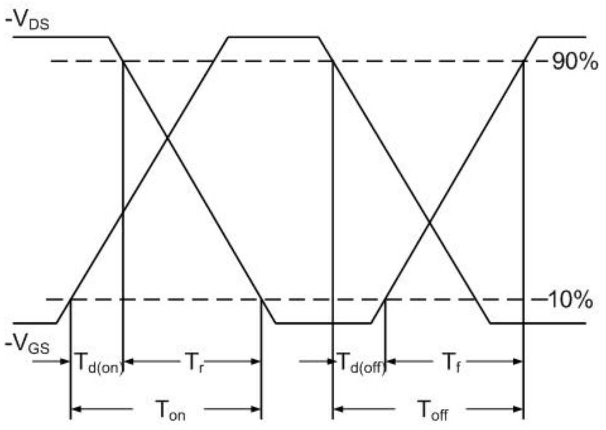


Fig.9 Normalized Maximum Transient Thermal Impedance



$$EAS=\frac{1}{2}L\times(-I_{AS}{}^2)\times\frac{-BV_{DSS}}{-BV_{DSS}-(-V_{DD})}$$

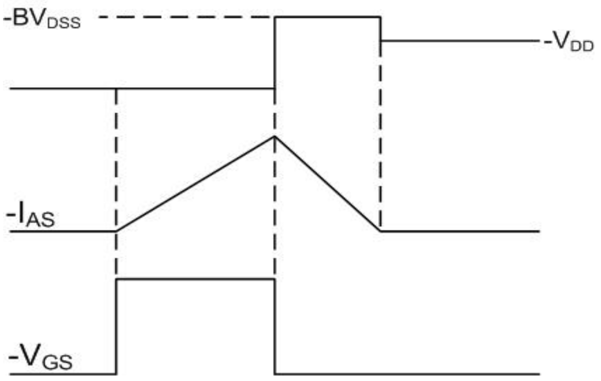
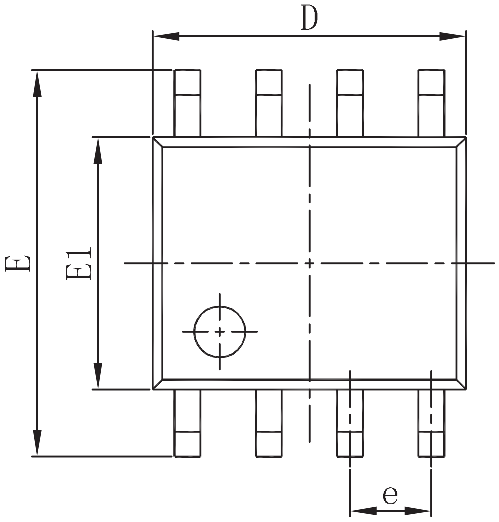
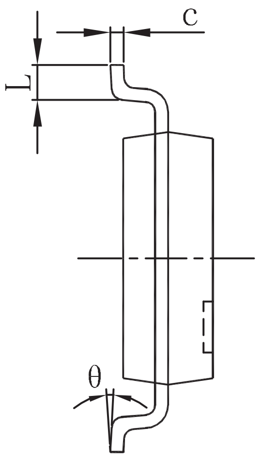


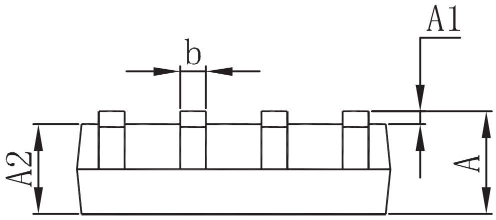
Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform

Packaging information







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1. 350	1. 750	0. 053	0. 069
A1	0. 100	0. 250	0. 004	0. 010
A2	1. 350	1. 550	0. 053	0. 061
b	0. 330	0. 510	0. 013	0. 020
c	0. 170	0. 250	0. 007	0. 010
D	4. 800	5. 000	0. 189	0. 197
e	1. 270（BSC）		0. 050（BSC）	
E	5. 800	6. 200	0. 228	0. 244
E1	3. 800	4. 000	0. 150	0. 157
L	0. 400	1. 270	0. 016	0. 050
θ	0°	8°	0°	8°